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The 28th Magnetic Recording Conference (TMRC2017) August 2 – 4, Tsukuba, Japan

The 28th Magnetic Recording Conference (TMRC 2017) will be held on **August 2 - 4**, **2017** at the Tsukuba International Congress Center in Tsukuba, Japan. TMRC 2017 will focus on future magnetic storage technologies for hard disk drives and solid state memories. 38 invited talks and 98 posters (including invited talks) will be presented. TMRC is known for it's high quality and leading announcements. Some highlights this year include:

Al technology innovation will change to storage and memory !? , Hirofumi Nagai Fujitsu, Plenary Lecture

New record HAMR areal density near 2Tbpsi using novel interlaced recording method, Seagate, D3.

HDD system level design on HAMR: energy-assisted recording system architecture and applications, WDC, D7

3D magnetic recording based on MAMR technology, Toshiba, E3

Tape is not dead, ways to achieve over 200 Gb/in² in tape recording, IBM, BP-02.

4Gbit STT-MRAM paves path for stand-alone MRAM applications, Hynix-Toshiba, C1.

SOT devices for high-speed memories and artificial synapses, Tohoku Univ. C2.

Voltage-control spintronics memory for high-density and high-speed applications Toshiba, F1

3D Integration Technology for STT-MRAM based on direct wafer bonding and backside silicon removal processes, AIST, C4.

High-MR lower-RA STT-MRAM with 10nm pillar diameter, TEL-AIST, C5.

Heusler-alloy-based MTJs with a Cu(In_{0.8}Ga_{0.2})Se₂ semiconductor barrier for low RA, NIMS, DP-05.

Register to TMRC2017!





